Excellent Integrated System Limited

Stocking Distributor

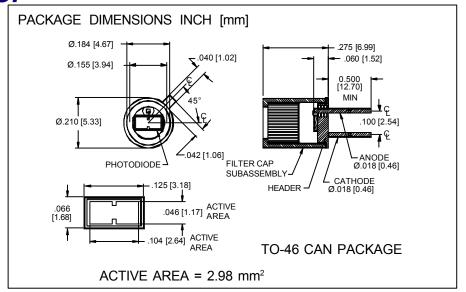
Click to view price, real time Inventory, Delivery & Lifecycle Information:

Advanced Photonix, Inc. PDV-C403-46

For any questions, you can email us directly: sales@integrated-circuit.com

PHOTONIC Silicon Photodiode, Filter Combination Photoconductive **DETECTORS INC.** 600 nm (red color) Type PDV-C403-46





FEATURES

- 600 nm CWL
- 65 nm FWHM
- Low noise

DESCRIPTION

The **PDV-C403-46** is a silicon, PIN planar diffused, photodiode with a red color 600 nm +/- 2 nm CWL wide band interference filter and a wide 65 nm half bandwidth. Ideal for photometry and radiometry measurment applications.

APPLICATIONS

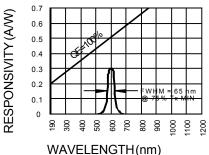
- Red color matching
- Color meters
- Film processing

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-20	+85	∞
То	Operating Temperature Range	-15	+70	∞
Ts	Soldering Temperature*		+240	∞
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current***	H = 100 fc, 2850 K	40	45		μ A
ΙD	Dark Current	H = 0, V _R = 10 V		.15	1.0	nA
R sH	Shunt Resistance	H = 0, V _R = 10 mV	.5	1.0		GΩ
TC Rsh	Rsн Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃
C₁	Junction Capacitance	H = 0, V _R = 10 V**		10		рF
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		600		nm
HBW	Half Bandwidth	(FWHM)		65		nm
V _{BR}	Breakdown Voltage	I = 10 μA	70	100		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1.5x10 ⁻¹⁴		W/√ Hz
tr	Response Time	RL = 1 KΩ V _R = 50 V		10		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f=1 MHz, ***without filter [FORM NO. 100-PDV-C403-46 REV N/C]